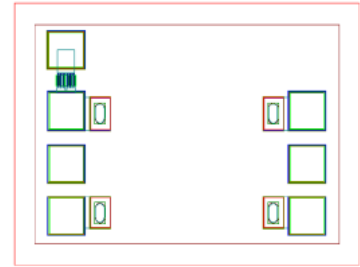


**AMT1617(L2)**  
**DC - 40GHz Temperature Compensated Attenuator Chip**



**Key Features :**

- Frequency range : DC – 40GHz
- Input/output standing wave : 1.2/12.
- Room temperature insertion loss : 5.3dB@10GHz, 5.5dB@25GHz
- Phase consistency :  $\leq |\pm 2|^\circ@10\text{GHz}$ ,  $\leq |\pm 5|^\circ@25\text{GHz}$
- Chip dimensions : 1.0mm x 0.75mm x 0.1mm
- Applications : wireless communication, transceiver module, radio telecommunication etc.

**Description :**

AMT1617(L2) is a temperature compensated attenuator chip, it is designed by Gallium Arsenide (GaAs) pHEMT process. Its core device is an electrical controlled attenuator whose attenuation is adjustable by a linear voltage, its control signal is generated by thermosensitive device. This chip is to stabilize the temperature-depended gain of a microwave amplifier.

**Absolute Maximum Ratings (Ta = 25°C)**

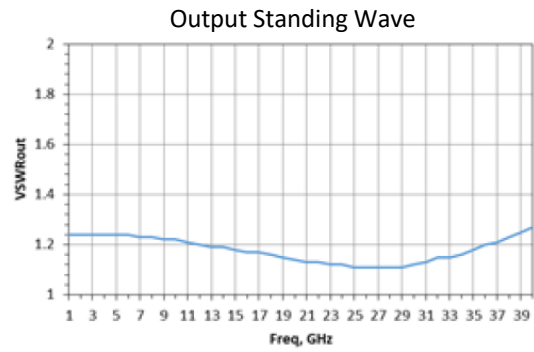
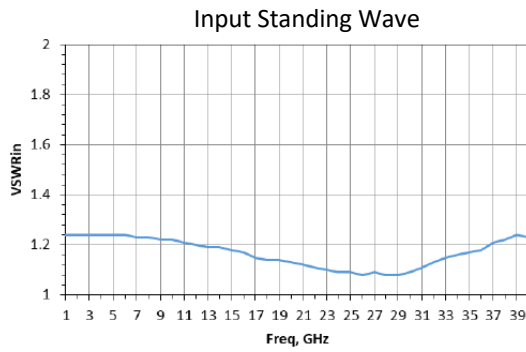
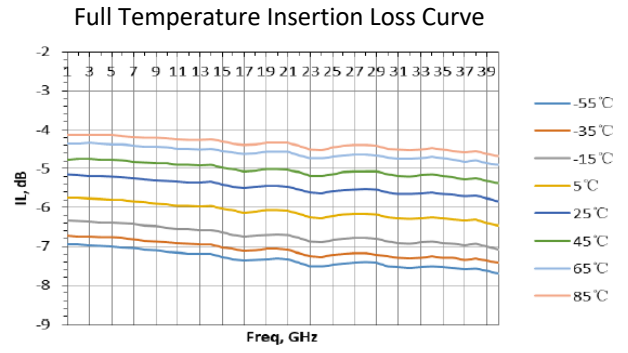
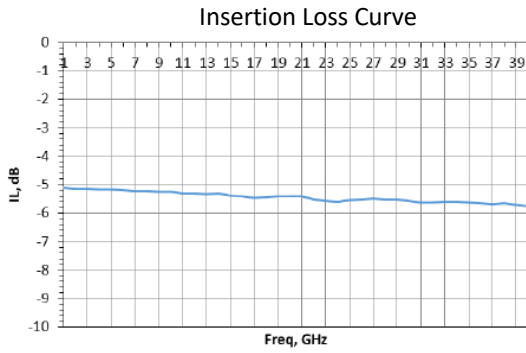
Symbol	Parameter	Value	Remark
VSS	Operation voltage	-6V	
Pin	Input Power	20dBm	
Tch	Operation Temperature	150°C	
Tm	Sintering Temperature	310°C	30s, N <sub>2</sub> protection
Tstg	Storage Temperature	-65 ~ +150°C	

[1] Operation outside any of the Absolute Maximum Ratings may cause permanent device damage.

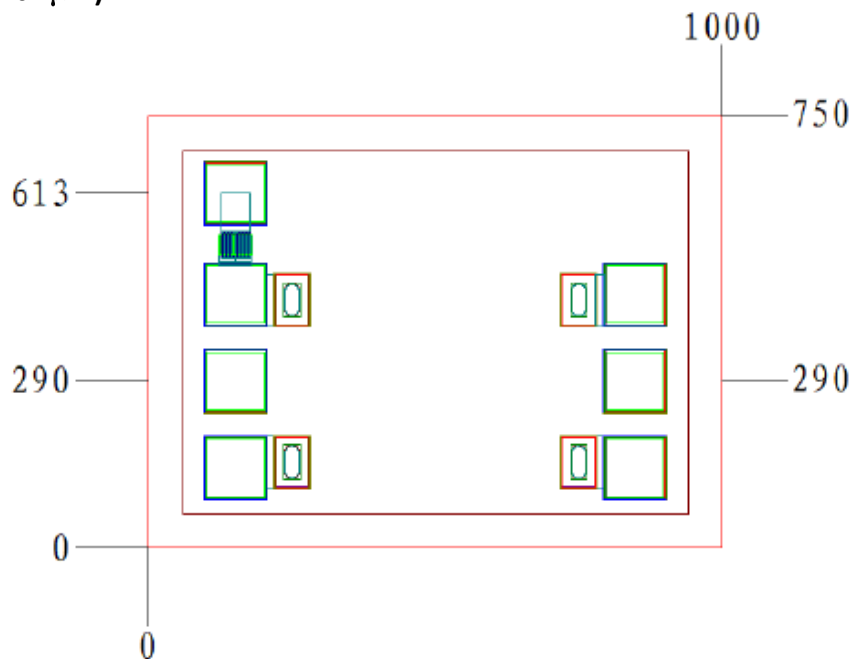
**Electrical Characteristics (Ta = 25°C)**

Symbol	Parameter	Value			Unit
		Min	Typical	Max	
F	Frequency range	DC - 40			GHz
IL	Insertion Loss	F = 10GHz	-	5.3	dB
		F = 25GHz	-	5.5	
ΔP	Phase consistency	F = 10GHz	-2	-	°
		F = 25GHz	-5	-	
VSWRin	Input Standing Wave	F = 1~40GHz	-	1.2	-
VSWRout	Output Standing Wave	F = 1~40GHz	-	1.2	-

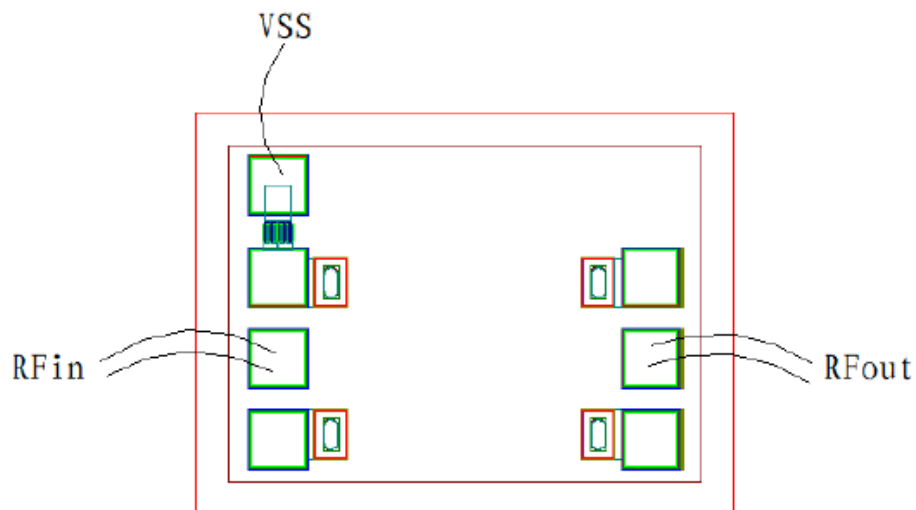
## Typical Performance



**Chip Dimensions (Unit :  $\mu\text{m}$ )**



**Chip Layout Diagram**



**Pad Definition**

No.	Symbol	Function	Dimension
1	RF_in	RF input pad	100 $\mu\text{m}$ *100 $\mu\text{m}$
2	RF_out	RF output pad	100 $\mu\text{m}$ *100 $\mu\text{m}$
3	VSS	-5V power supply	100 $\mu\text{m}$ *100 $\mu\text{m}$

Please see Appendix A for details.